ATTY DKT. NO.: AMAT/7589/CMP/ECP/RKK

U.S. SERIAL NO.: UNKNOWN

FILED: HEREWITH APPLICANT: APPLIED MATERIALS

TITLE: FORMATION OF PROTECTION LAYER BY DRIPPING DI ON

WAFER WITH HIGH ROTATION TO PREVENT STAIN FORMATION FROM

1202/H2S04 CHEMICAL SPLASH

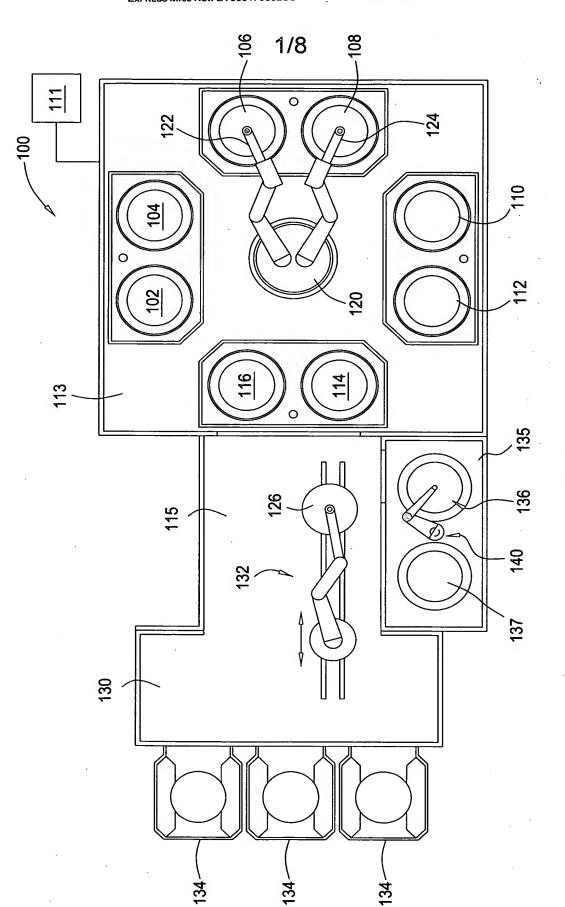
INVENTOR: BO ZHENG, ET AL.

EYEDESS MAIL NO: 5/33547080211S

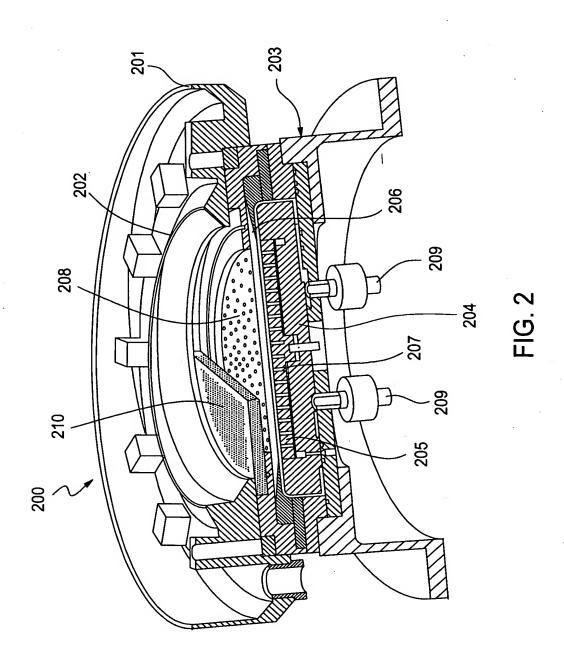
PAGE 1 OF 8

INVENTOR: BO ZHENG, ET AL EXPRESS MAIL NO.: EV335470802US

PAGE 1 OF 8



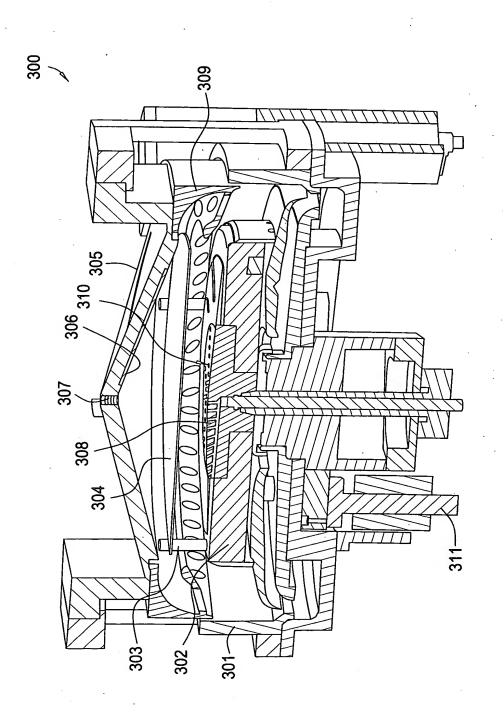
ATTY DKT. NO.: AMAT/7589/CMP/ECP/RKK
U.S. SERIAL NO.: UNKNOWN
FILED: HEREWITH APPLICANT: APPLIED MATERIALS
TITLE: FORMATION OF PROTECTION LAYER BY DRIPPING DI ON
WAFER WITH HIGH ROTATION TO PREVENT STAIN FORMATION FROM
1202/H2S04 CHEMICAL SPLASH
INVENTOR: BO ZHENG, ET AL.
EXPRESS MAIL NO.: EV335470802US PAGE 2 OF 8



ATTY DKT. NO.: AMAT/7589/CMP/ECP/RKK

U.S. SERIAL NO.: UNKNOWN CONF. NO.: UNKNOWN
FILED: HEREWITH APPLICANT: APPLIED MATERIALS
TITLE: FORMATION OF PROTECTION LAYER BY DRIPPING DI ON
WAFER WITH HIGH ROTATION TO PREVENT STAIN FORMATION FROM
1202/H2SO4 CHEMICAL SPLASH
INVENTOR: BO ZHENG, ET AL.

EXPRESS MAIL NO.: EV335470802US PAGE 3 OF 8



ATTY DKT. NO.: AMAT/7589/CMP/ECP/RKK

U.S. SERIAL NO.: UNKNOWN

FILED: HEREWITH APPLICANT: APPLIED MATERIALS

TITLE: FORMATION OF PROTECTION LAYER BY DRIPPING DI ON

WAFER WITH HIGH ROTATION TO PREVENT STAIN FORMATION FROM

H2O2/H2SO4 CHEMICAL SPLASH

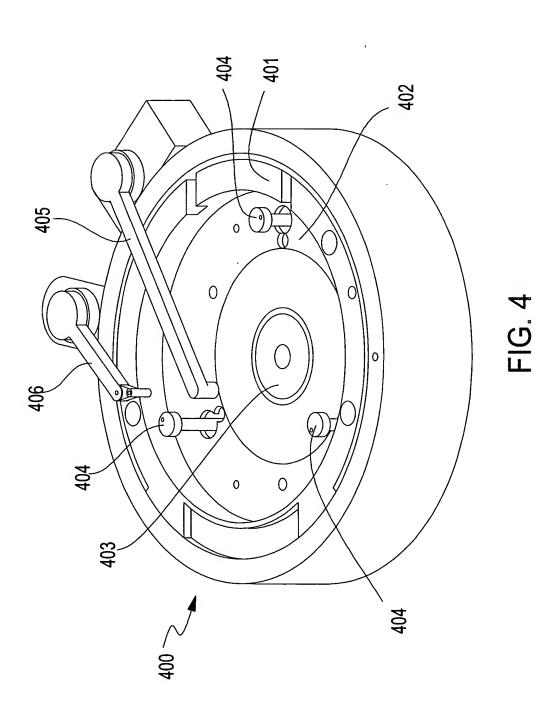
INVENTOR: BO ZHENG, ET AL.

EVERBESS MAIL NO.: EV/3254/708021IS

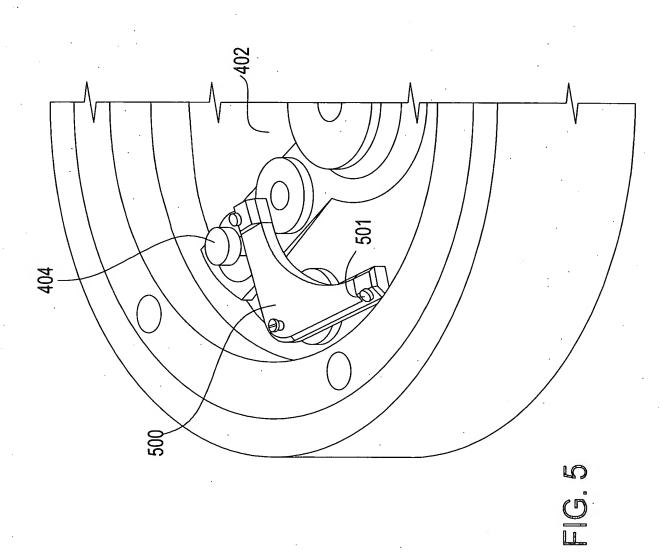
PAGE 4 OF 8

 Γ

EXPRESS MAIL No.: EV335470802US PAGE 4 OF 8



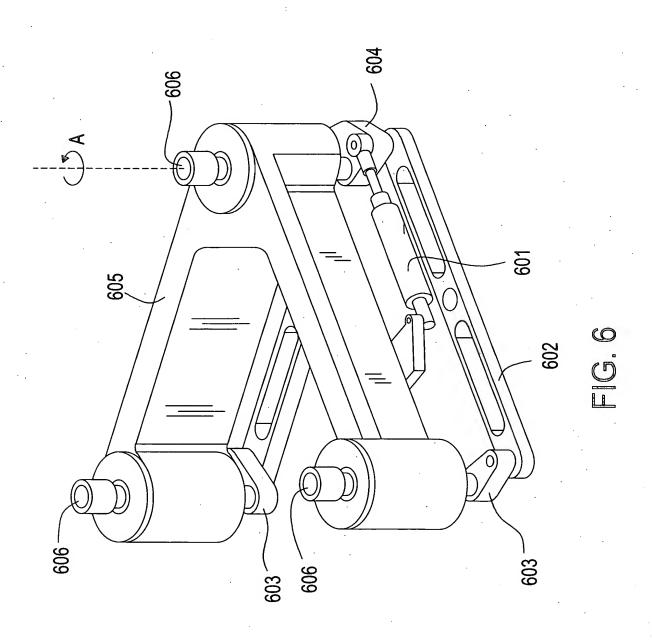
ATTY DKT. NO.: AMAT/7589/CMP/ECP/RKK
U.S. SERIAL NO.: UNKNOWN CONF. NO.: UNKNOWN
FILED: HEREWITH APPLICANT: APPLIED MATERIALS
TITLE: FORMATION OF PROTECTION LAYER BY DRIPPING DI ON
WAFER WITH HIGH ROTATION TO PREVENT STAIN FORMATION FROM
1202/H2SO4 CHEMICAL SPLASH
INVENTOR: BO ZHENG, ET AL.
EXPRESS MAIL NO.: EV335470802US PAGE 5 OF 8



ATTY DKT. NO.: AMAT/7589/CMP/ECP/RKK
U.S. SERIAL NO.: UNKNOWN CONF. NO.: UNKNOWN
FILED: HEREWITH APPLICANT: APPLIED MATERIALS
TITLE: FORMATION OF PROTECTION LAYER BY DRIPPING DI ON
WAFER WITH HIGH ROTATION TO PREVENT STAIN FORMATION FROM
H2O2/H2SO4 CHEMICAL SPLASH

INVENTOR: BO ZHENG, ET AL. EXPRESS MAIL NO.: EV335470802US

PAGE 6 OF 8



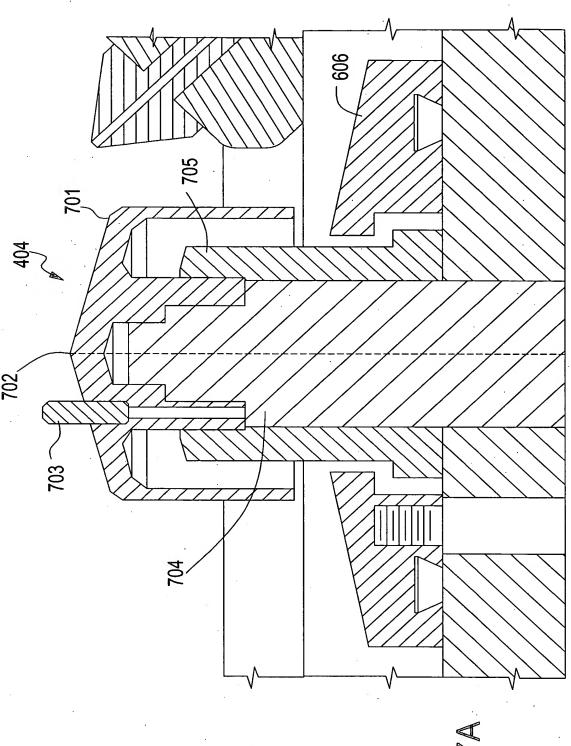
ATTY DKT. NO.: AMAT/7589/CMP/ECP/RKK

U.S. SERIAL NO.: UNKNOWN CONF. NO.: UNKNOWN
FILED: HEREWITH APPLICANT: APPLIED MATERIALS
TITLE: FORMATION OF PROTECTION LAYER BY DRIPPING DI ON
WAFER WITH HIGH ROTATION TO PREVENT STAIN FORMATION FROM
1202/H2SO4 CHEMICAL SPLASH
INVENTOR: BO ZHENG, ET AL.

EXPRESS MAIL NO.: EV33547080211S
PAGE 7 OF 8

EXPRESS MAIL No.: EV335470802US

PAGE 7 OF 8



ATTY DKT. NO.: AMAT/7589/CMP/ECP/RKK
U.S. SERIAL NO.: UNKNOWN
FILED: HEREWITH APPLICANT: APPLIED MATERIALS
TITLE: FORMATION OF PROTECTION LAYER BY DRIPPING DI ON
WAFER WITH HIGH ROTATION TO PREVENT STAIN FORMATION FROM
H2O2/H2SO4 CHEMICAL SPLASH
INVENTOR: BO ZHENG, ET AL.
EXPRESS MAIL NO.: EV335470802US PAGE 8 OF 8



